L	Hits	Search Text	DB	Time stamp
Number	11100			-
1	5	941123.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/03
2	26	titanium adj alloy near12 (zinc or zn or cadmium or cd or mercury or hg or aluminium or aluminium or al or gallium or ga or indium or tin or sn or silicon or si or germanium or ge or lead or pb or antimony or sb or as or arsenic) and memory and circuit and titanium adj silicide and (257/\$6.ccls. or 438/\$6.ccls. or 365/\$6.ccls.) and contact	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/03
3	2	("6284316").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/03 13:50
4	2	("6143362").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/03
5	62	(bpsg or (borophosphosilicate or boro-phosphosilicate or (boro-phospho-silicate or borophospho-silicate) adj glass)) and memory.ti,ab,clm. and (ti or titanium) near2 alloy and (257/\$6.ccls. or 438/\$6.ccls. or 365/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/03 16:52
6	19	(bpsg or (borophosphosilicate or boro-phosphosilicate or (boro-phospho-silicate or borophospho-silicate) adj glass)) and memory.ti,ab,clm. and (ti or titanium) near2 alloy and (257/\$6.ccls. or 438/\$6.ccls. or 365/\$6.ccls.) and titanium adj silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/03 17:56
7	61	,	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/03 17:59

		(112 C41 201 2 A TIC C20 20 4 A	IICDAT.	2003/05/03
8	51	(US-6413812-\$ or US-6388284-\$ or US-6429449-\$ or US-6320213-\$ or	USPAT; US-PGPUB	17:58
		US-6222273-\$ or US-6208016-\$ or	05 13505	
	1	US-5851882-\$ or US-5985698-\$ or		
		US-6103612-\$ or US-6118135-\$ or		
		US-6121086-\$ or US-6153490-\$ or	İ	
		US-6177314-\$ or US-6198151-\$ or		
		US-6555431-\$ or US-6534781-\$ or		
		US-6461957-\$ or US-6455875-\$ or		
		US-6451665-\$ or US-5831276-\$ or		
		US-5440158-\$ or US-5210047-\$ or		1
		US-5102827-\$ or US-5084418-\$ or		
	i	US-4984196-\$ or US-4811078-\$).did. or		Į
}		(US-4636833-\$ or US-5495117-\$ or		
		US-5483487-\$ or US-5475240-\$ or		
	-	US-5580814-\$ or US-5745336-\$).did. or		
l .		(US-20020182859-\$ or US-20020182858-\$ or		
		US-20020177302-\$ or US-20020177292-\$ or		
		US-20020123216-\$ or US-20020109233-\$ or		
		US-20020079483-\$ or US-20020056862-\$ or		<u> </u>
		US-20020031887-\$ or US-20020020835-\$ or		
		US-20020003252-\$ or US-20010028082-\$ or		
		US-20030030148-\$ or US-20030030147-\$ or US-20030006414-\$ or US-20010002708-\$ or		
		US-20010001208-\$ or US-20010002708-\$ or		
		US-20010001208-\$ OF US-20010020900-\$ OF US-20010020900-\$		
9	51	memory.ti,ab,clm. and (ti or titanium)	USPAT;	2003/05/03
"	"	near2 alloy and (257/\$6.ccls. or	US-PGPUB;	19:17
		438/\$6.ccls. or 365/\$6.ccls.) and	EPO; JPO;	
		titanium adj silicide and ((US-6413812-\$	DERWENT;	
		or US-6388284-\$ or US-6429449-\$ or	IBM_TDB	
		US-6320213-\$ or US-6222273-\$ or		
		US-6208016-\$ or US-5851882-\$ or		
		US-5985698-\$ or US-6103612-\$ or		
	į į	US-6118135-\$ or US-6121086-\$ or		
		US-6153490-\$ or US-6177314-\$ or		
		US-6198151-\$ or US-6555431-\$ or US-6534781-\$ or US-6461957-\$ or		
		US-6455875-\$ or US-6451665-\$ or		
	ļ	US-5831276-\$ or US-5440158-\$ or		
	Ì	US-5210047-\$ or US-5102827-\$ or		
		US-5084418-\$ or US-4984196-\$ or		
		US-4811078-\$).did. or (US-4636833-\$ or		
		US-5495117-\$ or US-5483487-\$ or		
		US-5475240-\$ or US-5580814-\$ or		
		US-5745336-\$).did. or (US-20020182859-\$		
1	-	or US-20020182858-\$ or US-20020177302-\$		
	1	or US-20020177292-\$ or US-20020123216-\$		
	[or US-20020109233-\$ or US-20020079483-\$	1	
		or US-20020056862-\$ or US-20020031887-\$		
		or US-20020020835-\$ or US-20020003252-\$		
		or US-20010028082-\$ or US-20030030148-\$ or US-20030030147-\$ or US-20030006414-\$		
		or US-20030030147-\$ or US-20030006414-\$ or US-20010001208-\$		
		or US-20010002/08-\$ or US-20010001208-\$		
		US-20010022374-\$).did.)		
10	13	1	USPAT;	2003/05/03
10	13	II AI W REGIO GITOY	US-PGPUB;	19:35
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	678	(257/754).CCLS.	USPAT;	2003/05/03
~ ~		, , , , , , ,	US-PGPUB;	19:35
1			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
12	2		USPAT;	2003/05/03
		silicide or "ti si.sub.2") and titanium	US-PGPUB;	19:36
-		near6 alloy and memory.ti,ab,clm.	EPO; JPO;	
	1		DERWENT;	1
1	1		IBM TDB	

	140	(257/486).CCLS.	USPAT;	2003/05/03
-	140	(257/400).CCL3.	US-PGPUB	13:22
_	203	((257/642) or (257/643)).CCLS.	USPAT;	2001/09/27
	3.5	(057/C45) GGTS	US-PGPUB USPAT;	11:18 2001/09/27
-	36	(257/645).CCLS.	US-PGPUB	11:19
_	53	(257/651).CCLS.	USPAT;	2001/09/27
			US-PGPUB USPAT;	11:19
_	612	(257/751).CCLS.	US-PGPUB	11:19
_	278	(257/752).CCLS.	USPAT;	2001/09/27
			US-PGPUB USPAT;	11:19
-	182	(257/753).CCLS.	US-PGPUB	11:20
_	389	(257/754).CCLS.	USPAT;	2001/09/27
		· · · · · · · · · · · · · · · · · · ·	US-PGPUB USPAT;	11:20
-	210	(257/757).CCLS.	US-PGPUB	11:20
_	194	(257/759).CCLS.	USPAT;	2001/09/27
		(057/760)	US-PGPUB USPAT;	11:20
-	307	(257/760).CCLS.	US-PGPUB	11:20
-	155	(257/761).CCLS.	USPAT;	2001/09/27
	0.5.1	(257/7CE) CCIS	US-PGPUB USPAT;	11:20
-	251	(257/765).CCLS.	US-PGPUB	11:20
_	371	(257/766).CCLS.	USPAT;	2001/09/27
	234	(257/767).CCLS.	US-PGPUB USPAT;	11:20 2001/09/27
-	234	(25777077.0013.	US-PGPUB	11:21
-	251	(257/768).CCLS.	USPAT;	2001/09/27
	248	(257/770).CCLS.	US-PGPUB USPAT;	2001/09/27
-	240	(237) 770) . 3013 .	US-PGPUB	11:21
-	132	(257/642).CCLS.	USPAT; US-PGPUB	2001/09/27
_	97	(257/643).CCLS.	USPAT;	2001/09/27
			US-PGPUB	11:21
-	36	(257/645).CCLS.	USPAT; US-PGPUB	2001/09/27 11:21
_	53	(257/651).CCLS.	USPAT;	2001/09/27
			US-PGPUB USPAT;	11:21 2001/09/27
_	985	(257/758).CCLS.	US-PGPUB	11:22
_	2061	(("257/486").CCLS.) or ((("257/642") or	USPAT;	2001/09/27
		("257/643")).CCLS.) or	US-PGPUB; EPO; JPO;	11:23
		(("257/645").CCLS.) or (("257/651").CCLS.) or	DERWENT;	
1		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or (("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or (("257/760").CCLS.)		
_	2341	1 ''	USPAT;	2001/09/27
		(("257/765").CCLS.) or	US-PGPUB;	11:24
		(("257/766").CCLS.) or (("257/767").CCLS.) or	EPO; JPO; DERWENT;	
		(("257/768").CCLS.) or	IBM_TDB	
		(("257/770").CCLS.) or		
		(("257/642").CCLS.) or (("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.)		

		/////	*****	2001/00/27
-	369	(((("257/486").CCLS.) or ((("257/642") or	USPAT;	2001/09/27
		("257/643")).CCLS.) or	US-PGPUB;	11:25
		(("257/645").CCLS.) or	EPO; JPO;	1
		(("257/651").CCLS.) or	DERWENT;]
		(("257/751").CCLS.) or	IBM TDB	
1		(("257/752").CCLS.) or		
1				
		(("257/753").CCLS.) or		
		(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
		(("257/765").CCLS.) or]
		(("257/766").CCLS.) or		1
		(("257/766").CCLS.) or		į
	1			
		(("257/768").CCLS.) or		
		(("257/770").CCLS.) or		
1		(("257/642").CCLS.) or		
1		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.))) and fluorin\$4		
			PDO. TDO.	2001/09/27
_	554	fluorin\$4 and integrated adj circuit	EPO; JPO;	2001/09/27
1			DERWENT;	11:26
		·	IBM_TDB	
_	65	(((((("257/486").CCLS.) or ((("257/642")	USPAT;	2001/09/27
		or ("257/643")).CCLS.) or	US-PGPUB;	13:35
1		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
				l i
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or		
		(("257/ 7 54").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
		, , ,		
		(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
		(("257/767").CCLS.) or		
		(("257/768").CCLS.) or		
		(("257/770").CCLS.) or		
		(("257/642").CCLS.) or		
		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/651").CCLS.))) and fluorin\$4) or		
		(fluorin\$4 and integrated adj circuit))		
		and substrate and (silicon same (tantalum		
		or tantalum adj nitride or tantalum adj		
		silicide or cobalt or cobalt adj		
		silicide))		
_	33	I	USPAT;	2001/09/27
		("6274933") or ("6262485") or ("6211561")	US-PGPUB;	13:36
		or ("6157081") or ("6097095") or	EPO; JPO;	
		OL		
		("5719416") or ("5675185") or ("5668394")	DERWENT;	ļ
1		or ("5585673") or ("5306951") or	IBM_TDB	
		("5138432") or ("4675073")).PN.		
-	2	jp-11354464\$-\$.did.	USPAT;	2001/09/27
			US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	1	///!/620150/!!\ (!!6277720!!\	USPAT;	2001/09/27
-	35			
		("6274933") or ("6262485") or ("6211561")	US-PGPUB;	13:44
		or ("6157081") or ("6097095") or	EPO; JPO;	
		("5719416") or ("5675185") or ("5668394")	DERWENT;	
	1	or ("5585673") or ("5306951") or	IBM_TDB	
		("5138432") or ("4675073")).PN.) or	_	
		jp-11354464\$-\$.did.		
1	1	JE 1. m		<u> </u>

		(#C277720#) or	USPAT;	2001/09/27
-	8	(((("6281584") or ("6277730") or ("6274933") or ("6262485") or ("6211561")	US-PGPUB;	13:44
		or ("6157081") or ("6097095") or	EPO; JPO;	
		("5719416") or ("5675185") or ("5668394")	DERWENT;	
İ	1	or ("5585673") or ("5306951") or	IBM_TDB	
		("5138432") or ("4675073")).PN.) or		
		jp-11354464\$-\$.did.) and (fluorine near10		
		barrier)		
		6277730.pn.	USPAT;	2001/09/27
-	1 1	02///30.p	US-PGPUB;	16:39
ļ	!		EPO; JPO;	ì
			DERWENT;	
			IBM_TDB	2001/00/27
_	320	fluorine adj2 silicon adj (oxide or	USPAT;	2001/09/27
		dioxide)	US-PGPUB;	16:41
			EPO; JPO;	
			DERWENT; IBM TDB	
			USPAT;	2001/09/27
-	87	fluorine adj2 silicon adj dioxide	US-PGPUB;	16:46
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
ļ	245	fluorine adj2 silicon adj oxide	USPAT;	2001/09/27
-	243	Truotino aaja omatera aaj	US-PGPUB;	16:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2001/09/27
_	1	6281584.pn.	USPAT;	17:14
			US-PGPUB; EPO; JPO;	17.14
İ			DERWENT;	
			IBM TDB	1
		fluorinated adj silicon adj dioxide adj	USPAT;	2001/09/27
_	0	fluorinated adj silicon adj dioxide adj "(sio"\$4	US-PGPUB;	17:17
		(810.34	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	275	"(sio\$3)"	USPAT;	2001/09/27
			US-PGPUB;	17:19
1			EPO; JPO;	
			DERWENT; IBM TDB	
		n ADAM and Elmonisated	USPAT;	2001/09/27
-	7	"(sio\$3)" and fluorinated	US-PGPUB;	17:26
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004 (50 (27
_	183	silicon adj monoxide and 257/\$5.ccls.	USPAT;	2001/09/27
		-	US-PGPUB;	17:27
		ł	EPO; JPO;	
			DERWENT; IBM TDB	
		las de la companiada de	USPAT;	2001/09/27
_	14		US-PGPUB;	17:28
		257/\$5.ccls.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	(fluorinated near10 silicon adj monoxide)	USPAT;	2001/09/27
_		and 257/\$5.ccls.	US-PGPUB;	17:28
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	2001/09/27
-	56	fsg adj film	USPAT;	2001/09/27
			US-PGPUB; EPO; JPO;	11.74
			DERWENT;	
			IBM TDB	

				10001/00/07
_	3	fsg adj film same dioxide	USPAT;	2001/09/27
			US-PGPUB;	17:42
			EPO; JPO;	ļ
			DERWENT;	1
			IBM_TDB	
_	2	jp-10035152\$-\$.did.	USPAT;	2001/09/27
			US-PGPUB;	20:23
			EPO; JPO;	
	-		DERWENT;	
			IBM_TDB	0001 (00 (07
_	0	yuasa.in. and fluorine and interconnect	JPO	2001/09/27
				20:23
_	0	yuasa.in. and fluorine and barrier	JPO	2001/09/27
				20:23
-	27	yuasa.in. and fluorine	JPO	2001/09/27
				20:26
-	28	yuasa.in. and fluorine	JPO;	2001/09/27
			DERWENT	20:26
-	1	yuasa.in. and fluorine	DERWENT	2001/09/27
				20:27
_	0	yuasa.in. and "035152"	JPO	2001/09/27
				20:28
-	1	yuasa.in. and fluorine	DERWENT	2001/09/27
			1	20:28
_	1	6281584.pn.	USPAT;	2001/09/28
			US-PGPUB;	10:11
	ļ		EPO; JPO;	
			DERWENT;	
			IBM_TDB	2001/00/29
-	5205		USPAT;	2001/09/28
		("257/643")).CCLS.) or	US-PGPUB;	10:28
	ł	(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or		
		(("257/754").CCLS.) or		
1		(("257/757").CCLS.) or		1
1		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
-		(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
	1	(("257/767").CCLS.) or (("257/768").CCLS.) or		
		(("257/768").CCLS.) or		
		(("257/642").CCLS.) or		
		(("257/642").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.))		

				2221/22/22
_	6	(((("257/486").CCLS.) or ((("257/642") or	USPAT;	2001/09/28
		("257/643")).CCLS.) or	US-PGPUB;	10:39
		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
,			IBM TDB	
		(("257/751").CCLS.) or	TDM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or		
		(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
	1			
		(("257/759").CCLS.) or		
	ļ	(("257/760").CCLS.)) or		
	ĺ	((("257/761").CCLS.) or		
	ļ	(("257/765").CCLS.) or		
	1	(("257/766").CCLS.) or		
ļ		(("257/767").CCLS.) or		
1	1	(("257/768").CCLS.) or	İ	
		(("257/770").CCLS.) or		<u> </u>
		(("257/642").CCLS.) or		
	1	(("257/643").CCLS.) or		1
	1			ļ
	Į l	(("257/645").CCLS.) or		
	1	(("257/651").CCLS.) or	ļ	
		(("257/758").CCLS.))) and fluorine adj2]
		barrier		1
1_	0	(((("257/486").CCLS.) or ((("257/642") or	USPAT;	2001/09/28
-	"		US-PGPUB;	10:40
		("257/643")).CCLS.) or	1	
1		(("257/645").CCLS.) or	EPO; JPO;]
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or	-	
		(("257/753").CCLS.) or		
	}	(("257/754").CCLS.) or		
1		(("257/757").CCLS.) or		
1		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
		(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
		(("257/767").CCLS.) or	İ	
		(("257/768").CCLS.) or		Ì
		(("257/770").CCLS.) or	1	
		' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '		
		(("257/642").CCLS.) or		
		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		1
		(("257/758").CCLS.))) and fluorine adj1		
				ļ
	_	barrier same tasin	USPAT;	2001/09/28
-	0	(((("257/486").CCLS.) or ((("257/642") or	i .	
		("257/643")).CCLS.) or	US-PGPUB;	10:40
1	1	(("257/645").CCLS.) or	EPO; JPO;	
1		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM TDB	
	1	(("257/752").CCLS.) or		
1	Ì	(("257/753").CCLS.) or		
		(("257/754").CCLS.) or		1 .
		(("257/757").CCLS.) or		
	1	(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		(('Z)//'00'').CCL3.)) OI		
		((("257/761").CCLS.) or		
		(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
1		(("257/767").CCLS.) or		
		(("257/768").CCLS.) or		
		((23//100).CCLB.) OI	1	
	1	(("257/770").CCLS.) or	İ	
		(("257/642").CCLS.) or		
1		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/643").CCLS.) or		1
		((25//051).CCL5.) OI		
1	1	(("257/758").CCLS.))) and (fluorine adj1		
		barrier and tasin)		
		The state of the s		

				0001/00/00
[-	2	(((("257/486").CCLS.) or ((("257/642") or	USPAT;	2001/09/28
	ļ	("257/643")).CCLS.) or	US-PGPUB;	10:42
		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or		
		(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
Ì		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
		(("257/765").CCLS.) or		
	İ	(("257/766").CCLS.) or		ļ
1 .		(("257/767").CCLS.) or		
		(("257/768").CCLS.) or		
		(("257/770").CCLS.) or		
		(("257/642").CCLS.) or		1
		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
	ĺ	(("257/651").CCLS.) or		
		(("257/758").CCLS.))) and (fluorine adj1		
		barrier and (tasin or tantalum))		2001/00/20
-	2		USPAT;	2001/09/28
		("257/643")).CCLS.) or	US-PGPUB;	10:49
		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or	1	
1		(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
		(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
		(("257/767").CCLS.) or		
		(("257/768").CCLS.) or		
1		(("257/770").CCLS.) or		
1		(("257/642").CCLS.) or		
		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.))) and (fluorine adj1		
		barrier and (tasin or tantalum)) and		
		(@rlad<20000414)	HCDAM -	2001/09/29
-	0		USPAT;	2001/09/28
		("257/643")).CCLS.) or	US-PGPUB;	10:50
		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or		
1		(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or		
1		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
		(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
		(("257/767").CCLS.) or		
		(("257/768").CCLS.) or		
		(("257/770").CCLS.) or		
		(("257/642").CCLS.) or		
		(("257/643").CCLS.) or		
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.))) and (fluorine adj1		
		barrier same (tasin or tantalum or cobalt		
		or silicide)) and (@rlad<20000414)		

- 0 (((("257/486").CCLS.) or ((("257/642") or USPAT;	2001/09/28
("257/643")).CCLS.) or US-PGPUB;	10:51
(("257/645").CCLS.) or EPO; JPO;	
(("257/651").CCLS.) or DERWENT;	
(("257/751").CCLS.) or IBM_TDB	
(("257/752").ccls.) or	
(("257/753").ccls.) or	
(("257/754").CCLS.) or	
(("257/757").CCLS.) or	
(("257/759").CCLS.) or	
(("257/760").CCLS.)) or	
((("257/761").CCLS.) or	
(("257/765").CCLS.) or	
(("257/766").CCLS.) or	1
(("257/767").CCLS.) or	
(("257/768").CCLS.) or	
(("257/770").CCLS.) or	
(("257/642").CCLS.) or	
(("257/643").CCLS.) or	
(("257/645").CCLS.) or	
(("257/651").CCLS.) or	
(("257/758").CCLS.))) and (fluorine adj2	
barrier same (tasin or tantalum or cobalt	1
or silicide)) and (@rlad<20000414)	
0 (((("257/486").CCLS.) or ((("257/642") or USPAT;	2001/09/28
("(('257/400').ccls.) or US-PGPUB;	10:51
(("257/645").CCLS.) or EPO; JPO;	
(("257/651").CCLS.) or DERWENT;	
(("257/751").CCLS.) or IBM_TDB	
(("257/752").CCLS.) or	
(("257/752").CCLS.) or	
(("257/754").CCLS.) or	
(("257/757").CCLS.) or	
(("257/759").CCLS.) or	
(("257/760").CCLS.)) or	
((257/760).ccls.) or	
((("257/765").CCLS.) or	
(("257/766").CCLS.) or	
(("257/767").CCLS.) or	
(("257/768").CCLS.) or	
(("257/770").CCLS.) or	
(("257/642").CCLS.) or	
(("257/643").CCLS.) or	
(("257/645").CCLS.) or	
(("257/651").CCLS.) or	
(("257/758").CCLS.))) and (fluorine adj2	
barrier same (tasin or tantalum or cobalt	
	1

				******	2001/00/20
			(((25), 100) 000=== ((== : , = =)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/28
-	-		(("257/643").CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or (("257/758").CCLS.))) and (fluorine same diffusion adj barrier same (tasin or tantalum or cobalt or silicide)) (((("257/486").CCLS.) or ((("257/642") or	USPAT;	2001/09/28
			("257/643")).CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or (("257/751").CCLS.) or (("257/752").CCLS.) or (("257/753").CCLS.) or (("257/754").CCLS.) or (("257/759").CCLS.) or (("257/760").CCLS.) or (("257/761").CCLS.) or (("257/766").CCLS.) or (("257/766").CCLS.) or (("257/768").CCLS.) or (("257/768").CCLS.) or (("257/768").CCLS.) or (("257/7642").CCLS.) or (("257/642").CCLS.) or (("257/645").CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or (("257/758").CCLS.) or (("257/758").CCLS.) or (("257/758").CCLS.)) or (("257/758").CCLS.))) and (fluorine same diffusion adj barrier same (tasin or tantalum or cobalt or silicide or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	11:10
	-	2	silicon)) 6265779.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/28 13:24
	-	0	(graded near5 diffusion adj barrier) and fluorin\$4 and dielectric and (integrated adj circuit or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/28 14:34
	-	0	fluorin\$4 and dielectric and (integrated adj circuit or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/28 14:35
	-	0	<pre>(graded near5 (diffusion adj barrier or cap\$4 adj (layer or film))) and fluorin\$4 and dielectric and (integrated adj circuit or substrate)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/28 14:37

-	364	graded and fluorin\$ and barrier	USPAT;	2001/09/28
			US-PGPUB;	14:37
			EPO; JPO;	
İ			DERWENT;	
			IBM TDB	
_	209	graded and fluorin\$ and barrier and	USPAT;	2001/09/28
	200	silicon	US-PGPUB;	14:38
1		51110011	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	70	graded and fluorin\$ and barrier and	USPAT;	2001/09/28
-	'0	silicon and (tantalum or cobalt)	US-PGPUB;	14:39
		Silicon and (cancaram or conser,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	34	graded and fluorin\$ and barrier and	USPAT;	2001/09/28
-	34	silicon and (tantalum or cobalt) and	US-PGPUB;	14:39
		@rlad<20000414	EPO; JPO;	
		@riad<20000414	DERWENT;	
			IBM TDB	İ
	24	graded and fluorin\$ and barrier and	USPAT;	2001/09/28
-	34	silicon and (tantalum or cobalt) and	US-PGPUB;	14:40
			EPO; JPO;	11111
		@rlad<20000404	DERWENT;	
			IBM TDB	
		1 1 Cl	USPAT;	2001/09/28
-	15	graded and fluorin\$ and barrier and	US-PGPUB;	15:00
		silicon and (tantalum or cobalt) and	EPO; JPO;	13.00
		@rlad<20000404 and (257/\$5.ccls. or	DERWENT;	
		438/\$5.ccls.)	IBM TDB	
			EPO; JPO;	2001/09/28
-	0	graded and fluorin\$ and barrier and	DERWENT;	15:01
		silicon and (tantalum or cobalt) and	IBM TDB	15.01
		Grlad<20000404 and (dielectric and	IBM_IDB	
	_	substrate)	EPO; JPO;	2001/09/28
-	0	graded and fluorin\$ and barrier and	DERWENT;	15:01
		silicon and (tantalum or cobalt) and		13.01
		(dielectric and substrate)	IBM_TDB USPAT;	2001/09/28
-	0	graded adj barrier and 257/\$5.ccls. and	US-PGPUB;	15:42
		(fluorin\$4 near10 dielectric)	EPO; JPO;	13.42
			DERWENT;	
			IBM TDB	
		1 057/451-	USPAT;	2001/09/28
-	33	graded adj2 barrier and 257/\$5.ccls.	US-PGPUB;	15:42
		•	EPO; JPO;	15.42
	ļ			
ļ			DERWENT;	
) 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB USPAT;	2001/09/28
-	1	graded adj2 barrier and 257/\$5.ccls. and		16:04
		fluorin\$4	US-PGPUB;	10.04
			EPO; JPO;	1
			DERWENT; IBM TDB	
1			_	2001/09/28
-	0	57720527.pn.	USPAT;	15:56
			US-PGPUB;	15.56
-			EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	2001/09/28
-	3	5770520.pn.	USPAT;	15:56
			US-PGPUB;	13.30
			EPO; JPO;	
			DERWENT;	
		1 055 /45	IBM_TDB	2001/09/29
-	74777	graded adj barrier layer and 257/\$5.ccls.	USPAT;	2001/09/28
			US-PGPUB;	16:05
			EPO; JPO;	
	1		DERWENT;	
- 1	1		IBM_TDB	

Γ-	-	1	graded adj barrier adj layer.ti. and	USPAT;	2001/09/28
			257/\$5.ccls.	US-PGPUB;	16:22
				EPO; JPO;	
				DERWENT;	
				IBM_TDB	
-	-	0	graded adj barrier and fluorin\$2	EPO; JPO;	2001/09/28
1	İ			DERWENT;	16:29
				IBM_TDB	
١.	-	0	graded adj tantalum adj silicide	USPAT;	2001/09/28
			-	US-PGPUB;	16:31
				EPO; JPO;	
				DERWENT;	
	İ			IBM_TDB	
.	-	13	(silicon near10 tantalum) same graded	USPAT;	2001/09/28
				US-PGPUB;	16:32
				EPO; JPO;	
				DERWENT;	
				IBM_TDB	((
	-	7	((silicon near10 tantalum) same graded)	USPAT;	2001/09/28
1			and barrier	US-PGPUB;	16:33
				EPO; JPO;	
				DERWENT;	
Ì				IBM_TDB	0001/00/00
	-	242	(tantalum near5 silicon) same (barrier or	USPAT;	2001/09/28
			cap\$4) adj2 (layer or film)	US-PGPUB;	16:57
				EPO; JPO;	,
				DERWENT;	
				IBM_TDB	2001/09/28
	-	46	(tantalum near5 silicon) same (barrier or	USPAT;	17:04
			cap\$4) adj2 (layer or film) and	US-PGPUB;	17:04
			257/\$5.ccls.	EPO; JPO;	
				DERWENT;	
ĺ		_	(homion on	IBM_TDB USPAT;	2001/09/28
	-	0	(tantalum near5 silicon) same (barrier or	US-PGPUB;	17:05
			cap\$4) adj2 (layer or film) and 257/\$5.ccls and fluorin\$4	EPO; JPO;	17.00
			25//\$5.CCIS and IIuOIIII\$4	DERWENT;	
				IBM TDB	
		33	(tantalum near5 silicon) same (barrier or	USPAT;	2001/09/28
-	-	33	cap\$4) adj2 (layer or film) and fluorin\$4	US-PGPUB;	17:06
-			capyi, adje (layer of lilm, and flatelin,	EPO; JPO;	
ı				DERWENT;	
				IBM TDB	l i
	_	2	(tantalum near5 silicon) same (barrier or	USPAT;	2001/09/28
ı	ļ	_	cap\$4) adj2 (layer or film) same	US-PGPUB;	17:07
			fluorin\$4	EPO; JPO;	
				DERWENT;	
	ļ			IBM_TDB	
	_	0	(barrier or capping or cap) adj (layer	USPAT;	2001/09/29
			adj film adj region)	US-PGPUB;	18:46
-				EPO; JPO;	
				DERWENT;	
				IBM_TDB	2001/00/20
	_	60203		USPAT;	2001/09/29
			film or region)	US-PGPUB;	18:47
				EPO; JPO;	
				DERWENT;	
			1.0	IBM_TDB USPAT;	2001/09/29
	_	11894	((barrier or capping or cap) adj (layer	US-PGPUB;	18:55
		1	or film or region)) and (257/\$5.ccls. or		15.55
			438/\$5.ccls.)	EPO; JPO; DERWENT;	
				IBM TDB	
		2225	///hammian an anning on can't add /larran	USPAT;	2001/09/29
	-	3818	(((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or	US-PGPUB;	18:58
		1	438/\$5.ccls.)) and (silicon near10	EPO; JPO;	-3.00
-			(barrier or capping or cap))	DERWENT;	
			(battiet of capping of cap/)	IBM TDB	
- 1		4	1	,	1

				0001/00/20
_	416	((((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or 438/\$5.ccls.)) and (silicon near10	USPAT; US-PGPUB; EPO; JPO;	2001/09/29 18:59
		(barrier or capping or cap))) and (tantalum or cobalt) near10 (barrier or capping or cap)	DERWENT; IBM_TDB	
-	1	(((((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or 438/\$5.ccls.)) and (silicon near10 (barrier or capping or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/09/29 18:59
		(cap))) and (tantalum or cobalt) near10 (barrier or capping or cap)) and (fluorin\$4 near (barrier or cap or capping))	IBM_TDB	
	12200	((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or 438/\$5.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/29 18:56
_	3862	(((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or 438/\$5.ccls.)) and (silicon near10 (barrier or capping or cap))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/29 18:56
-	420	((((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or 438/\$5.ccls. or 313/\$5.ccls.)) and (silicon near10 (barrier or capping or cap))) and (tantalum or cobalt) near10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/29 18:57
-	1	(barrier or capping or cap) (((((barrier or capping or cap) adj (layer or film or region)) and (257/\$5.ccls. or 438/\$5.ccls. or 313/\$5.ccls.)) and (silicon near10 (barrier or capping or cap))) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/29 18:57
_	6939	(tantalum or cobalt) near10 (barrier or capping or cap)) and (fluorin\$4 near (barrier or cap or capping)) ((barrier or capping or cap) adj (layer	USPAT;	2001/09/29
		or film or region)) and (silicon near10 (barrier or capping or cap))	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	18:58
_	552	(((barrier or capping or cap) adj (layer or film or region)) and (silicon near10 (barrier or capping or cap))) and (tantalum or cobalt) near10 (barrier or capping or cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/29 18:59
_	16		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/29 19:01
_	1	<pre>cap or capping)) ((((barrier or capping or cap) adj (layer or film or region)) and (silicon near10 (barrier or capping or cap))) and</pre>	USPAT; US-PGPUB; EPO; JPO;	2001/09/29 19:01
	0	(tantalum or cobalt) near10 (barrier or capping or cap)) and (fluorin\$4 near (barrier or cap or capping)) (graded near4 (cap or capping or	DERWENT; IBM_TDB USPAT;	2001/09/29
		barrier)) and (fluorin\$4 near4 (barrier or cap or capping)) and (silicon near4 (barrier or cap or capping)) and ((tantalum or cobalt) near4 (barrier or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	19:08
-	. 2	<pre>cap or capping)) (fluorin\$4 near4 (barrier or cap or capping)) and (silicon near4 (barrier or cap or capping)) and ((tantalum or cobalt) near4 (barrier or cap or</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2001/09/29 20:07
		capping))	IBM_TDB	

				100 100
_	1483	(adhesion or adhesive or bonding) same	USPAT;	2001/09/29
		((barrier or cap or capping) adj (layer	US-PGPUB;	20:11
		or film or region)) and (257/\$5.ccls. or	EPO; JPO;	
		438/\$5.ccls.)	DERWENT; IBM TDB	
	534	(adhesion or adhesive or bonding) adj	USPAT;	2001/09/29
_	534	(layer or film or region) same ((barrier	US-PGPUB;	20:12
		or cap or capping) adj (layer or film or	EPO; JPO;	
ı		region)) and (257/\$5.ccls. or	DERWENT;	
		438/\$5.ccls.)	IBM TDB	
ı -	106	(adhesion or adhesive or bonding) adj	USPAT;	2001/09/29
		(laver or film or region) same ((barrier	US-PGPUB;	20:14
		or cap or capping) adj (layer or film or	EPO; JPO;	
		region)) and (257/\$5.ccls. or	DERWENT;	
		438/\$5.ccls.) and fluorin\$4	IBM_TDB	2001 (00 (20
-	27	(adhesion or adhesive or bonding) adj	USPAT;	2001/09/29
		(layer or film or region) same ((barrier	US-PGPUB;	20:15
		or cap or capping) adj (layer or film or	EPO; JPO; DERWENT;	
		region)) and (257/\$5.ccls. or 438/\$5.ccls.) and (fluorin\$4 same	IBM TDB	
		barrier)	1011_100	
{ _	19	(adhesion or adhesive or bonding) adj	USPAT;	2001/09/29
-	19	(layer or film or region) same ((barrier	US-PGPUB;	20:18
		or cap or capping) adj (layer or film or	EPO; JPO;	
Į l		region)) and (257/\$5.ccls. or	DERWENT;	
		438/\$5.ccls.) and (fluorin\$4 same	IBM_TDB	
		(barrier or cap or capping) adj (layer		
		or film or region)) and ((tantalum or		
]		silicon or cobalt) near10 (barrier or cap		
1		or capping))	11CDATT•	2001/09/30
-	1	6277730.pn.	USPAT; US-PGPUB;	15:24
			EPO; JPO;	13.21
!			DERWENT;	
			IBM TDB	
_	1	6281584.pn.	USPAT;	2001/09/30
	1		US-PGPUB;	19:26
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2001/00/20
-	1	6252303.pn.	USPAT;	2001/09/30
			US-PGPUB; EPO; JPO;	10.07
			DERWENT;	
			IBM TDB	
	0	(257/\$5.ccls. or 438/\$5.ccls.) and	USPAT;	2001/09/30
] -		depleted same fluorine same barrier same	US-PGPUB;	17:24
		adhesi\$2	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	48	(("5946601") or ("6281584") or	USPAT;	2001/09/30
		("6252303") or ("6022766") or ("6287990")	US-PGPUB;	19:03
		or ("5675185") or ("6277730") or	EPO; JPO;	
		("6274933") or ("6262485") or ("6211561")	DERWENT;	
		or ("6157081") or ("5138432") or	IBM_TDB	
		("6097095") or ("5719416") or ("5668394")		
	1	or ("5585673") or ("5306951") or		
		("4675073") or ("6265779") or ("6184550") or ("6265779") or ("5942769") or		
		("6284657") or ("6054398")).PN.		
1_	23		USPAT	2001/09/30
	23	("6252303") or ("6022766") or ("6287990")		19:03
		or ("5675185") or ("6277730") or		
		("6274933") or ("6262485") or ("6211561")		
1		or ("6157081") or ("5138432") or		
		("5000005") ("5710416") ("5660204")	1	
		("6097095") or ("5719416") or ("5668394")	1	
		or ("5585673") or ("5306951") or		
		or ("5585673") or ("5306951") or ("4675073") or ("6265779") or ("6184550")		
		or ("5585673") or ("5306951") or		,

				0001 (00 (30
-	18	((("5946601") or ("6281584") or	USPAT;	2001/09/30
		("6252303") or ("6022766") or ("6287990")	US-PGPUB;	19:03
		or ("5675185") or ("6277730") or	EPO; JPO;	
ļ		("6274933") or ("6262485") or ("6211561")	DERWENT;	
l		or ("6157081") or ("5138432") or	IBM_TDB	
		("6097095") or ("5719416") or ("5668394")		
		or ("5585673") or ("5306951") or		
		("4675073") or ("6265779") or ("6184550")		
		or ("6265779") or ("5942769") or		
[İ	("6284657") or ("6054398")).PN.) and		
		interconnect\$3		2001 (00 (20
-	14	((("5946601") or ("6281584") or	USPAT;	2001/09/30
		("6252303") or ("6022766") or ("6287990")	US-PGPUB;	19:10
		or ("5675185") or ("6277730") or	EPO; JPO;	
		("6274933") or ("6262485") or ("6211561")	DERWENT;	
		or ("6157081") or ("5138432") or	IBM_TDB	
		("6097095") or ("5719416") or ("5668394")		
1		or ("5585673") or ("5306951") or		
		("4675073") or ("6265779") or ("6184550")		
		or ("6265779") or ("5942769") or		
		("6284657") or ("6054398")).PN.) and		
		(interconnect\$3 same (copper or aluminum		
		or aluminium or tungsten or molybdenum or		
ļ		silver or gold or tantalum adj nitride or		
		titanium adj nitride))	**************************************	2001/00/20
-	3	((("5946601") or ("6281584") or	USPAT;	2001/09/30
		("6252303") or ("6022766") or ("6287990")	US-PGPUB;	19:12
		or ("5675185") or ("6277730") or	EPO; JPO;	
		("6274933") or ("6262485") or ("6211561")	DERWENT;	
		or ("6157081") or ("5138432") or	IBM_TDB	
		("6097095") or ("5719416") or ("5668394")		
		or ("5585673") or ("5306951") or		
		("4675073") or ("6265779") or ("6184550")		
		or ("6265779") or ("5942769") or		
1		("6284657") or ("6054398")).PN.) and		
		(interconnect\$3 same (copper or aluminum		
		or aluminium or tungsten or molybdenum or		
		silver or gold or tantalum adj nitride or		
		titanium adj nitride) same (fsg or		
		fluorosilicate or fluorinated) same		
1		(barrier or cap or capping or		
		passivation))	USPAT;	2001/09/30
-	723	(257/\$5.ccls. or 438/\$5.ccls.) and	US-PGPUB;	19:31
		fluorin\$4 and (barrier or passivation or	EPO; JPO;	17.51
1		passivated or cap or capping) and	DERWENT;	
1		(dielectric or capacitance) and (interconnect\$3 same (copper or aluminium	IBM TDB	
	İ	or aluminum or tungsten or molybdenum or	12120	
		silver or gold or titanium adj nitride or		
	1	tantalum adj nitride))		
	100	1	USPAT;	2001/09/30
-	192	(fluorin\$4 same (barrier or passivation	US-PGPUB;	19:32
		or passivated or cap or capping)) and	EPO; JPO;	
		(dielectric or capacitance) and	DERWENT;	
		(interconnect same (copper or aluminium	IBM TDB	
		or aluminum or tungsten or molybdenum or		
		silver or gold or titanium adj nitride or		
		tantalum adj nitride))		
	17	(257/758.ccls.) and (fluorin\$4 same	USPAT;	2001/09/30
-	1/	(barrier or passivation or passivated or	US-PGPUB;	19:33
		cap or capping)) and (dielectric or	EPO; JPO;	
		cap or capping) and (differences same	DERWENT;	
		capacitance) and (interconnect same (copper or aluminium or aluminum or	IBM TDB	
		tungsten or molybdenum or silver or gold	1011_100	
		or titanium adj nitride or tantalum adj		
l .		nitride))		L

		/////BOEZ/406#N GGTG N am ///BOEZ/640#N	USPAT;	2002/04/19
-	6931	((((("257/486").CCLS.) or ((("257/642")	US-PGPUB;	09:15
	-	or ("257/643")).CCLS.) or		09.13
		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM_TDB	
		(("257/752").CCLS.) or		
		(("257/753").CCLS.) or		
	ļ.	(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or		
1		(("257/760").CCLS.)) or		
		((("257/761").CCLS.) or		
	1	(("257/765").CCLS.) or		
		(("257/766").CCLS.) or		
1		(("257/766").CCLS.) or		
		(("257/768").CCLS.) or		
		(("257/770").CCLS.) or		
		(("257/642").CCLS.) or		
		(("257/643").CCLS.) or	}	
		(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.))) and fluorin\$4) or		
		(fluorin\$4 and integrated adj circuit)		
-	564	(((((("257/486").CCLS.) or ((("257/642")	USPAT;	2002/04/19
İ		or ("257/643")).CCLS.) or	US-PGPUB;	09:17
		(("257/645").CCLS.) or	EPO; JPO;	
		(("257/651").CCLS.) or	DERWENT;	
		(("257/751").CCLS.) or	IBM TDB	
		(("257/752").CCLS.) or	_	
		(("257/753").CCLS.) or		
		(("257/754").CCLS.) or		
		(("257/757").CCLS.) or		
		(("257/759").CCLS.) or		
		(("257/760").CCLS.)) or		İ
		((257/760).CCLS.) or		
		(("257/761").CCLS.) or		
		(("257/766").CCLS.) or		1
		(("257/767").CCLS.) or		
		(("257/768").CCLS.) or		
		(("257/770").CCLS.) or		
	-	(("257/642").CCLS.) or		
		(("257/643").CCLS.) or		
	İ	(("257/645").CCLS.) or		
		(("257/651").CCLS.) or		
		(("257/758").CCLS.))) and fluorin\$4) or		
İ	1			
		(fluorin\$4 and integrated adj circuit)) and (fluorin\$4 near3 polymer\$2)		

_	63	((((((("257/486").CCLS.) or ((("257/642") or ("257/643")).CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 09:24
		(("257/751").CCLS.) or (("257/752").CCLS.) or (("257/753").CCLS.) or (("257/754").CCLS.) or (("257/757").CCLS.) or	IBM_TDB	
		(("257/759").CCLS.) or (("257/760").CCLS.)) or ((("257/761").CCLS.) or (("257/765").CCLS.) or (("257/766").CCLS.) or (("257/767").CCLS.) or		
		(("257/768").CCLS.) or (("257/770").CCLS.) or (("257/642").CCLS.) or (("257/643").CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or		
		(("257/758").CCLS.))) and fluorin\$4) or (fluorin\$4 and integrated adj circuit)) and (fluorin\$4 near3 polymer\$2)) and (barrier near3 diffusion)		
_	25	((((((("257/486").CCLS.) or ((("257/642") or ("257/643")).CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or (("257/751").CCLS.) or (("257/752").CCLS.) or (("257/753").CCLS.) or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19
		(("257/754").CCLS.) or (("257/757").CCLS.) or (("257/759").CCLS.) or (("257/760").CCLS.)) or ((("257/761").CCLS.)) or		
		(("257/765").CCLS.) or (("257/766").CCLS.) or (("257/767").CCLS.) or (("257/768").CCLS.) or (("257/770").CCLS.) or (("257/642").CCLS.) or		
		(("257/643").CCLS.) or (("257/645").CCLS.) or (("257/651").CCLS.) or (("257/758").CCLS.))) and fluorin\$4) or (fluorin\$4 and integrated adj circuit)) and (fluorin\$4 near3 polymer\$2)) and (barrier near3 diffusion)) and diffusion adj barrier and polymer\$2 near3		
_	8	<pre>dielectric and (ic or integrated adj circuit) diffusion adj barrier near6 polymer\$2</pre>	USPAT;	2002/04/19
		near6 dielectric and (ic or integrated adj circuit)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	12:07
	5	(diffusion adj barrier near6 polymer\$2 near6 dielectric and (ic or integrated adj circuit)) and (bcb or benzocyclobutarene or benzocyclobutene or cyclotene or poly adj arylene adj ether or poly-arylene adj ether or silk or polyimide or aromatic adj hydrocarbon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 12:14

-	2	(diffusion adj barrier near6 polymer\$2	USPAT;	2002/04/19	
		near6 dielectric and (ic or integrated	US-PGPUB;	12:17	
		adj circuit)) and ((bcb or benzocyclobutene or	EPO; JPO;		
		cyclotene or poly adj arylene adj ether	DERWENT; IBM TDB		
1		or poly-arylene adj ether or silk or	IDM_IDB		
		polyimide or aromatic adj hydrocarbon)	İ		
		same barrier adj layer)			
-	767	((bcb or benzocyclobutarene or	USPAT;	2002/04/19	
		benzocyclobutene or cyclotene or poly adj	US-PGPUB;	12:18	
		arylene adj ether or poly-arylene adj	EPO; JPO;		
		ether or silk or polyimide or aromatic	DERWENT;		ı
	32	adj hydrocarbon) same barrier adj layer)	IBM_TDB		
_	32		USPAT;	2002/04/19	
		benzocyclobutene or cyclotene or poly adj	US-PGPUB;	12:20	
		arylene adj ether or poly-arylene adj ether or silk or polyimide or aromatic	EPO; JPO;		ł
		adj hydrocarbon) with barrier adj layer)	DERWENT;		
		and integrated adj circuit.ti,ab.	IBM_TDB		-
_	0	((bcb or benzocyclobutarene or	USPAT;	2002/04/19	
	1	benzocyclobutene or cyclotene or poly adj	US-PGPUB;	12:20	
		arylene adj ether or poly-arylene adj	EPO; JPO;		
		ether or silk or polyimide or aromatic	DERWENT;		
		adj hydrocarbon) with barrier adj layer	IBM_TDB		
		with fluorinated) and integrated adj			
_	8	circuit.ti,ab.			
] 8	((bcb or benzocyclobutarene or benzocyclobutene or cyclotene or poly adj	USPAT;	2002/04/19	
		arylene adj ether or poly-arylene adj	US-PGPUB;	12:21	
		ether or silk or polyimide or aromatic	EPO; JPO; DERWENT;		-
		adj hydrocarbon) with barrier adj layer	IBM TDB		
		with fluorinated)			
_	7	((bcb or benzocyclobutarene or	USPAT;	2002/04/19	
		benzocyclobutene or cyclotene or poly adj	US-PGPUB;	12:30	
		arylene adj ether or poly-arylene adj	EPO; JPO;		1
	1	ether or silk or polyimide or aromatic	DERWENT;		
		adj hydrocarbon) with barrier adj layer with fluorinated) and (257/\$6.ccls. or	IBM_TDB		
		438/\$6.ccls.)			
_	22	((pfcb or perfluorocyclobutane or	USPAT;	2002/04/19	
		fluorinated polyethylene or ptfe or	US-PGPUB;	13:44	ı
		polytetrafluoroethylene or fluorinated	EPO; JPO;	20.11	
		adj parylene) with barrier adj layer with	DERWENT;		
		fluorinated) and (257/\$6.ccls. or	IBM_TDB		
:	_	438/\$6.ccls.)	_		
-	2	("6284657").PN.	USPAT;	2002/04/19	
			US-PGPUB;	15:53	
			EPO; JPO;		
		İ	DERWENT;		
_	39	parylene-F	IBM_TDB USPAT;	2002/04/10	l
	"		US-PGPUB;	2002/04/19 16:02	1
			EPO; JPO;	10.02	
			DERWENT;		
			IBM TDB		
- i	9	(parylene-F or af-4 or	USPAT;	2002/04/19	
		polytetrafluoro-p-xylylene) same	US-PGPUB;	16:56	
		dielectric adj layer and (257/\$6.ccls. or	EPO; JPO;		
		438/\$6.ccls.)	DERWENT;		
_	2	Jaraded nearly (hanning and 1613	IBM_TDB		
	4	(graded near6 (barrier adj (film or layer))) same silicon same (ta or	USPAT;	2002/04/19	1
		tantalum or tantalum adj nitride or tan\$3	US-PGPUB;	17:04	
		or tantalum adj silicide or tan\$3 or	EPO; JPO; DERWENT;		
		cobalt or cobalt adj silicide or co or	IBM TDB		
		cosi\$3) and (integrated adj circuit or	-DII_1DD		
		257/\$6.ccls. or 438/\$6.ccls.)			

-	2	(graded near6 (barrier adj (film or layer))) same silicon same (ta or tantalum or tantalum adj nitride or tan\$3 or tantalum adj silicide or tasi\$3 or cobalt or cobalt adj silicide or co or cosi\$3) and (integrated adj circuit or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 17:05
_	5	ic) ((graded near12 (barrier adj (film or layer))) near12 silicon) and (ta or tantalum or tantalum adj nitride or tan\$3 or tantalum adj silicide or tasi\$3 or cobalt or cobalt adj silicide or co or cosi\$3) and (integrated adj circuit or ic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:00
	0	((graded near12 (barrier adj (film or layer))) near12 silicon) and (ta or tantalum or tantalum adj nitride or tan\$3 or tantalum adj silicide or tasi\$3 or cobalt or cobalt adj silicide or co or cosi\$3) and (integrated adj circuit or ic) and plurality	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/19 21:02
-	31	low-k adj dielectric and polymer\$2 and barrier adj (layer or film) and ((plurality near3 layer) or (alternat\$3 near3 (layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/19 21:04
-	25	low-k adj dielectric and polymer\$2 and barrier adj (layer or film) and ((plurality near3 layer) or (alternat\$3 near3 (layer or film))) and integrated adj circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/19 21:15
-	1	("6281584").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:19
	0	("adhesion adj layer same barrier adj layer same low-k adj dielectric").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:20
_	3	adhesion adj layer same barrier adj layer same low-k adj dielectric	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:21
	29	adhesion adj layer and barrier adj layer and low-k adj dielectric	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:22
_	0	(adhesion adj layer near20 barrier adj layer) near20 low-k adj dielectric	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:22
_	6	(adhesion adj layer near20 barrier adj layer) and low-k adj dielectric	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:32
-	0	(adhesion adj layer near20 cobalt adj silicide) and low-k adj dielectric	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/04/19 21:44
-	2	("6323555").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/19 22:31

-	3	("6323555")).PN.	USPAT	2002/04/19 22:32
_	60		USPAT;	2002/09/27
		dielectric same (fluorine of f) near4	US-PGPUB;	09:26
		barrier	EPO; JPO;	
			DERWENT; IBM TDB	
-	39	(fluorine or f or fluorinated) near4	USPAT;	2002/09/27
		dielectric same (fluorine of f) near4	US-PGPUB	09:55
		barrier and (semiconductor or		
		interconnect or integrated near2		
_	28	circuit).ti,ab,clm. (fluorine or f or fluorinated) near4	USPAT;	2002/09/27
		dielectric same (fluorine of f) near4	US-PGPUB	09:56
		barrier and (semiconductor or		
-		interconnect or integrated near2		
		circuit).ti,ab,clm. and (tantalum or		
l _	2	cobalt) (fluorine or f or fluorinated) near4	HCDAM.	2002/00/27
		dielectric same (fluorine of f) near4	USPAT; US-PGPUB	2002/09/27
1		barrier same (tantalum or cobalt) and	55 1010B	10.00
		(semiconductor or interconnect or		
_	0	integrated near2 circuit).ti,ab,clm.		0000/65/55
		(fluorine or f or fluorinated) near4 dielectric same (fluorine of f) near4	EPO; JPO; DERWENT;	2002/09/27
		barrier same (tantalum or cobalt) and	IBM_TDB	10.51
		(semiconductor or interconnect or		
		integrated near2 circuit).ti,ab,clm.		
_	0	\====================================	EPO; JPO;	2002/09/27
		dielectric near12 (fluorine of f) near12 barrier same (tantalum or cobalt) and	DERWENT; IBM TDB	10:52
		(semiconductor or interconnect or	100	
	_	integrated near2 circuit).ti,ab,clm.		
-	0	(fluorine or f or fluorinated) near12	EPO; JPO;	2002/09/27
		dielectric near12 (fluorine of f) near12 barrier near12 (tantalum or cobalt) and	DERWENT;	10:52
		(semiconductor or interconnect or	IBM_TDB	
		integrated near2 circuit).ti,ab,clm.		
-	4	(fluorine or f or fluorinated) near12	USPAT;	2002/09/27
		dielectric near12 (fluorine of f) near12	US-PGPUB	11:13
		barrier near12 (tantalum or cobalt) and (semiconductor or interconnect or		
		integrated near2 circuit).ti,ab,clm.		
_	4	(fluorine or f or fluorinated) near12	USPAT;	2002/09/27
		(insulat\$3 or dielectric) near12	US-PGPUB	11:14
		(fluorine of f) near12 barrier near12 (tantalum or cobalt) and (semiconductor		
	ļ	or interconnect or integrated near2		
	[circuit).ti,ab,clm.		
-	4	(((fluorine or f or fluorinated) near12	USPAT;	2002/09/27
		(insulat\$3 or dielectric)) or F-BPSG or	US-PGPUB	11:18
		fluorinated adj boro-phospho adj silicate adj glass) near12 (fluorine of f) near12		
		barrier near12 (tantalum or cobalt) and		
		(semiconductor or interconnect or		
	_	integrated near2 circuit).ti,ab,clm.		
-	5	(((fluorine or f or fluorinated) near12	USPAT;	2002/09/27
		(insulat\$3 or dielectric)) or F-BPSG or fluorinated adj boro-phospho adj silicate	US-PGPUB	11:19
		adj glass) near12 barrier near12		
		(tantalum or cobalt) and (semiconductor		
		or interconnect or integrated near2		
_	39	circuit).ti,ab,clm.		0000/05/55
	39	(fluorinated adj dielectric or F-BPSG or fluorinated adj boro-phospho adj silicate	USPAT; US-PGPUB;	2002/09/27 11:21
		adj glass).ti,ab,clm.	EPO; JPO;	11.61
			DERWENT;	
			IBM_TDB	

-	-	0		USPAT;	2002/09/27 11:23
İ			fluorinated adj boro-phospho adj silicate adj glass).ti,ab,clm.) and barrier near12	US-PGPUB; EPO; JPO;	11.23
			(cobalt adj silicide or tantalum adj	DERWENT;	
			silicide)	IBM_TDB	
.	-	14	((fluorinated adj dielectric or F-BPSG or	USPAT;	2002/09/27
			fluorinated adj boro-phospho adj silicate	US-PGPUB;	11:23
1			adj glass).ti,ab,clm.) and barrier near2	EPO; JPO; DERWENT;	
			layer	IBM TDB	
١.	_	8	(((fluorinated adj dielectric or F-BPSG	USPAT;	2002/09/27
		•	or fluorinated adj boro-phospho adj	US-PGPUB;	12:46
			silicate adj glass).ti,ab,clm.) and	EPO; JPO;	·
1			barrier near2 layer) and (cobalt or	DERWENT; IBM TDB	
			tantalum) tantalum adj (silicide or salicide)	USPAT;	2002/09/27
'	-	0	near12 barrier near12 fluorine	US-PGPUB;	12:48
			Healtz Ballier Modela =======	EPO; JPO;	
	ļ			DERWENT;	
			10.1	IBM_TDB	2002/09/27
	-	0	tantalum-silicon-nitride near12 barrier near12 fluorine	USPAT; US-PGPUB;	12:49
			nearlz fluorine	EPO; JPO;	12.19
		ĺ		DERWENT;	
	1			IBM_TDB	(-0 (00
	- [3	tantalum-silicon-nitride near12 barrier	USPAT;	2002/09/27
Ì	ļ			US-PGPUB; EPO; JPO;	14:03
		ļ		DERWENT;	
				IBM TDB	
	_	15	diffusion near4 fluorine adj ions	USPAT;	2002/09/27
		İ		US-PGPUB;	12:54
				EPO; JPO; DERWENT;	
				IBM TDB	
	_	0	(cobalt or cobalt-silicon or	USPAT;	2002/09/27
	_	Ĭ	cobalt-tantalum-silicon or	US-PGPUB;	14:06
	}		cobalt-tantalum or tantalum-cobalt or	EPO; JPO;	
			tantalum) near12 diffusion adj layer	DERWENT; IBM TDB	
ļ		156	near12 fluorine (cobalt or cobalt-silicon or	USPAT;	2002/09/27
	_	136	cobalt-tantalum-silicon or	US-PGPUB;	14:10
			cobalt-tantalum or tantalum-cobalt or	EPO; JPO;	
Ì		•	tantalum) near12 diffusion adj layer	DERWENT;	
			/ 1 2 3	IBM_TDB USPAT;	2002/09/27
	-	52	(cobalt or cobalt-silicon or cobalt-tantalum-silicon or	US-PGPUB;	14:11
	ļ		cobalt-tantalum or tantalum-cobalt or	EPO; JPO;	
		1	tantalum) near12 diffusion adj	DERWENT;	
ļ			layer.ti,ab,clm.	IBM_TDB	2002/09/27
	-	21	(cobalt adj silicide or cobalt-silicon or cobalt-tantalum-silicon or	USPAT; US-PGPUB;	14:12
			cobalt-tantalum or tantalum-cobalt or	EPO; JPO;	
			tantalum adj silicide) near12 diffusion	DERWENT;	
			adi laver.ti,ab,clm.	IBM_TDB	2002/00/27
	-	9	(cobalt adj silicide or cobalt-silicon or	USPAT; US-PGPUB;	2002/09/27
1			cobalt-tantalum-silicon or cobalt-tantalum or tantalum-cobalt or	EPO; JPO;	14.51
			tantalum adj silicide) near12 barrier adj	DERWENT;	
			laver.ti,ab,clm.	IBM_TDB	
	-	1	(cobalt adj silicide or cobalt-silicon or	USPAT;	2002/09/27
		1	cobalt-tantalum-silicon or	US-PGPUB;	14:28
- [cobalt-tantalum or tantalum-cobalt or tantalum adj silicide) near12 barrier adj	EPO; JPO; DERWENT;	
			layer.ti,ab,clm. and fluorine	IBM_TDB	
	_	4		USPAT;	2002/09/27
				US-PGPUB;	14:32
				EPO; JPO;	
				DERWENT; IBM TDB	
- 1		I .	I and the second		1

-	5	tantalum adj silicide near10 fluorinated	USPAT;	2002/09/27
			US-PGPUB;	14:38
			EPO; JPO;	
-			DERWENT; IBM TDB	
_	0	(ta-si or tantalum-silicon) near10	USPAT;	2002/09/27
		fluorinated	US-PGPUB;	14:39
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	(- =	USPAT;	2002/09/27
		(fluorinated or fsg)	US-PGPUB;	14:41
			EPO; JPO; DERWENT;	
			IBM TDB	
-	0	(USPAT;	2002/09/27
		(fluorinated or fsg)	US-PGPUB;	15:58
			EPO; JPO;	
			DERWENT;	
_	90	gamping adi lawar manu12 (adharian an	IBM_TDB	0000 (00 (00
Ì	30	capping adj layer near12 (adhesion or adhesive)	USPAT; US-PGPUB;	2002/09/27
		duicsive	EPO; JPO;	15:59
			DERWENT;	
<u> </u>			IBM TDB	
-	64	1 .11 2 2 1 (()	USPAT	2002/09/27
	_	adhesive)		16:12
-	5	\	USPAT	2002/09/27
		adhesion-promoting) adj2 (film or layer) same fluorinated same dielectric same		16:33
		barrier		İ
-	1	flac and fluorinated adj dielectric	USPAT	2002/09/27
				16:33
-	5	flac and dielectric	USPAT	2002/09/27
_	136	gamban many) malaman sama (61 61)		16:35
_	136	carbon near3 polymer same (flac or fdlc or amorphous adj carbon)	USPAT; US-PGPUB;	2002/09/27
		or amorphous adj carpon,	EPO; JPO;	10:37
			DERWENT;	1
			IBM TDB	
_	103		USPAT;	2002/09/27
		or amorphous adj carbon)	US-PGPUB;	16:37
			EPO; JPO;	
			DERWENT; IBM TDB	
_	93	carbon near3 polymer near3 (flac or fdlc	USPAT;	2002/09/27
		or amorphous adj carbon)	US-PGPUB;	18:20
			EPO; JPO;	
			DERWENT;	
_	57	fsg.ti,ab. and interconnect	IBM_TDB	2002/00/27
	3/	ray.cr, and interconnect	USPAT; US-PGPUB;	2002/09/27 19:33
			EPO; JPO;	19.33
			DERWENT;	
			IBM_TDB	
-	2	(fluorinated adj silicon adj oxide or	USPĀT;	2002/09/27
		"sio:f") same dielectric adj layer same	US-PGPUB;	19:35
		barrier adj layer same (tantalum or cobalt)	EPO; JPO;	
		CODATC)	DERWENT;	
_	12	fluorinated adj dielectric same (adhesion	IBM_TDB USPAT;	2002/09/28
		or adhesive) near2 layer same barrier	US-PGPUB;	12:57
			EPO; JPO;	,
			DERWENT;	
			IBM TDB	

-	1	fluorine same barrier adj layer same	USPAT;	2002/09/28
İ	İ	(cobalt adj silicide or tantalum adj	US-PGPUB;	13:21
		silicide or cobalt-silicon or	EPO; JPO;	
]	tantalum-silicon or	DERWENT;	
	1	cobalt-tantalum-silicon or	IBM TDB	
		cobalt-tantalum adj silicide or cobalt	-	
		adj cobalt-tantalum adj silicide)		
-	0	Duncon and arorogorio banc barrior	USPAT;	2002/09/28
		same (alternating or both adj side)	US-PGPUB;	13:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	0	fluorinated adj dielectric same barrier	USPAT;	2002/09/28
		same (alternating or both adj side or	US-PGPUB;	13:23
		sandwich\$2)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	l i
-	2	(("6284657") or ("5880018")).PN.	USPAT	2002/09/28
				15:29
-	0	(fluorinated near3 (dielectric or	USPAT;	2002/09/28
		polyethylene or parylene or amorphous adj	US-PGPUB;	15:38
		carbon or BPSG) or PTFE or PFCB or	EPO; JPO;	
		F-BPSG) near25 barrier near25 ((tantalum	DERWENT;	
		or cobalt) adj (silicide or silicon) or	IBM_TDB	
		tantalum-silicon or cobalt-silicon)		
-	0	(fluorinated near3 (dielectric or	USPAT;	2002/09/28
		polyethylene or parylene or amorphous adj	US-PGPUB;	15:45
		carbon or BPSG or boron adj phospho adj	EPO; JPO;	
		silicate adj glass or boron-phosphO adj	DERWENT;	ĺ
		silicate adj glass or	IBM_TDB	
		boron-phospho-silicate adj glass or		
		silicon adj (oxide or dioxide)) or	-	
		"sio:f" or PTFE or teflon or fsg or PFCB		
		or F-BPSG) near25 barrier near25]
		((tantalum or cobalt) adj (silicide or		
		silicon) or tantalum-silicon or		
		cobalt-silicon or tantalum-cobalt-silicon		
		or cobalt-tantalum-silicon)		
-	0	(fluorinated near3 (dielectric or	USPAT;	2002/09/28
		polyethylene or parylene or amorphous adj	US-PGPUB;	15:49
		carbon or BPSG or boron adj phospho adj	EPO; JPO;	
		silicate adj glass or boron-phosph0 adj	DERWENT;	
	j	silicate adj glass or	IBM_TDB	
		boron-phospho-silicate adj glass or		
	[silicon adj (oxide or dioxide)) or "sio:f" or PTFE or teflon or fsg or PFCB		
1		or F-BPSG) near25 barrier near25	İ	
		((tantalum or cobalt) adj (silicide or		
		silicon) or "tasi.sub.2" or		
}	ļ	tantalum-silicon or cobalt-silicon or		
İ	•	tantalum-cobalt-silicon or		
	1	cobalt-tantalum-silicon)		
_	ا م	(fluorinated near6 (dielectric or	IICDAM -	3003/00/33
	١	polyethylene or parylene or amorphous adj	USPAT;	2002/09/28
Ī	ĺ	carbon or BPSG or boron adj phospho adj	US-PGPUB;	15:51
[]	silicate adj glass or boron-phosph0 adj	EPO; JPO;	
ĺ		silicate adj glass or boron-phospho adj	DERWENT;	
l	l	boron-phospho-silicate adj glass or	IBM_TDB	
	ļ	silicon adj (oxide or dioxide)) or		
		"sio:f" or PTFE or teflon or fsg or PFCB		
		or F-BPSG) near25 barrier near25		
		((tantalum or cobalt) adj (silicide or		
		silicon) or "tasi.sub.2" or		
		tantalum-silicon or cobalt-silicon or	İ	
		tantalum-cobalt-silicon or	ļ	
		cobalt-tantalum-silicon)		
		variouzum DIIIOVII)		

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Silicate adj glass or horom-phospho-silicate adj glass or silicon adj (oxide or dioxide) or silicon adj (oxide or dioxide) or silicon adj (oxide or dioxide) or silicon or silicon or silicon or silicon or silicon or silicon or silicon or silicon or silicon or coni oxide silicide or silicon or coni oxide silicide oxide			silicate adi glass or boron-phosph0 adi		1
boron-phospho-silicate adj glass or silicon adj (oxide or dioxide) or "sio:f" or PTFE or teflon or fsg or PFCB or F-BPSG) same barrier same ((tantalum or cobalt) adj (silicide or silicon) or "tasi.sub.2" or "cosi or cantalum-silicon or cobalt-silicon or cobalt-silicon or tantalum-cobalt-silicon or cobalt-tantalum-silicon) or double adj jet same pracipitation same other adj methods	1			1	
Silicon adj (oxide or dioxide) or	}		boron-phospho-silicate adj glass or	12011_122	
"sio:f" or PTEE or teflon or fsg or PFCB or F-BPSG) same barrier same ((tantalum or cobalt) adj (silicide or silicon) or "tasi.sub.2" or "cosi or tantalum-silicon or cobalt-silicon or cobalt-silicon or tantalum-cobalt-silicon or cobalt-tantalum-silicon) double adj jet same precipitation same other adj methods USPAT: US-PGPUB; DERWENT; IBM TDB USPAT: US-PGPUB; DERWENT; IBM TDB USPAT: US-PGPUB; DERWENT; IBM TDB USPAT: US-PGPUB; DERWENT; IBM TDB USPAT: US-PGPUB; DERWENT; IBM TDB USPAT:			silicon adj (oxide or dioxide)) or		
Or F-BPSG) same barrier same ((tantalum or cobalt) adj (silicide or silicon) or "tasi.sub.2" or "cosi.sub.2" or tasi or cosi or tantalum-silicon or cobalt-silicon or tantalum-silicon) or double adj jet same precipitation same other adj methods	1		"sio:f" or PTFE or teflon or fsg or PFCB		
Or cobalt) adj (silicide or silicon) or "tasi.sub.2" or "cosi sub.2" or tasi or cosi or tantalum-silicon or cobalt-silicon or tantalum-cobalt-silicon or cobalt-tantalum-cobalt-silicon or cobalt-tantalum-silicon) or double adj jet same precipitation same other adj methods			or F-BPSG) same barrier same ((tantalum		1
cosi or tantalum-silicon or cobalt-silicon or tantalum-cobalt-silicon or cobalt-silicon or tantalum-cobalt-silicon or cobalt-tantalum-silicon) double adj jet same precipitation same other adj methods	1	ł	or cobalt) adj (silicide or silicon) or		
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Other adj methods					•
- 6321 precipitation adj2 "methods" USPAT: US-PGPUB; PRO; PDO; DERWENNT; IEM TDB USPAT: US-PGPUB; PRO; PDO; DERWENNT; IEM TDB USPAT: US-PGPUB; PRO; PDO; DERWENNT; IEM TDB USPAT: US-PGPUB; PRO; PDO; DERWENNT; IEM TDB USPAT: US-PGPUB; PRO; USPAT: US-PGPUB; PRO; USPAT: U	-	0	double adj jet same precipitation same	1	
- 6321 precipitation adj2 "methods" DERWENT; IBM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; ISM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; ISM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; ISM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; ISM TDB USPAT; US-PCPUB; EPO; JPO; DERWENT; ISM TDB USPAT; USPAT 2002/09/28 17:37 2002/09/28 17:38 2002/09/28 20			other adj methods		17:34
- 6321 precipitation adj2 "methods" USPAT: US-PGPUB; EPO: JPO: DERWENT; IBM TDB USPAT: USPAT: US-PGPUB; EPO: JPO: DERWENT; IBM TDB USPAT: USPA					
- 6321 precipitation adj2 "methods"				•]
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- 853 precipitation adj2 "methods".ti,ab,clm. EPO, JPO, DERWENT; ITM TDB USPAT; US-PGPUB; EPO, JPO, DERWENT; ITM TDB USPAT 1 ("4680612").PN. USPAT USPAT 17:38 2002/09/28 17:37 2002/09/28 17:38 2002/09/28 17:38 2002/09/28 17:38 2002/09/28 17:34 2002/09/28 17:43 2002/09/28 17:43 2002/09/28 17:44 2002/09/28 17:45 2002/09/28 2002/09/28 2002/09/28 2002/09/28			prosproución dajz methods		
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- 2 ("6323555").PN. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	_	103	(Cmos adj inverter.tl,ab,clm.) and	USPAT	
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1 fluorine adj diffusion adj barrier near12 (tantalum or ta) 1 fluorine adj diffusion adj barrier near12 (tantalum or ta) 28 FSG.ti. 2003/05/01 18:48 2003/05/01 18:50 2003/05/01 18:50 2003/05/02 18:50 2003/05/02 09:31 2003/05/02 09:31		30	delaresa in	_	0000/05/
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The fluorine adj diffusion adj barrier near12 fluorine adj diffusion adj barrier near12 (tantalum or ta) DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT;					TQ:48
fluorine adj diffusion adj barrier near12 (tantalum or ta) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
fluorine adj diffusion adj barrier near12 (tantalum or ta) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
Tendent (tantalum or ta) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; DERWENT;	_	1	fluorine adj diffusion adj barrier near12		2003/05/01
EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/05/02 US-PGPUB; EPO; JPO; DERWENT; DERWENT;			(tantalum or ta)		
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 28 FSG.ti. IBM_TDB USPAT; 2003/05/02 US-PGPUB; EPO; JPO; DERWENT; DERWENT;		ļ			
US-PGPUB; 09:31 EPO; JPO; DERWENT;		_ 1		IBM_TDB	
EPO; JPO; DERWENT;	-	28	FSG.ti.		
DERWENT;				1	09:31
IBM TDB					
	<u></u>			TRW_LDB	

-	2	and and Silicon day	USPAT;	2003/05/02
		glass	US-PGPUB;	09:43
			EPO; JPO;	
			DERWENT;	
		//8C204CE78\ DX \	IBM_TDB	
_	"	(("6284657").PN.) and cobalt	USPAT;	2003/05/02
			US-PGPUB;	09:43
			EPO; JPO;	
			DERWENT;	
_	2	(UC204CE7U) DV	IBM_TDB	
_		("6284657").PN.	USPAT;	2003/05/02
			US-PGPUB;	11:26
			EPO; JPO;	
			DERWENT;	
_	2	("6294396").PN.	IBM_TDB	2000 (05 (00
		(0294396).PN.	USPAT;	2003/05/02
			US-PGPUB;	11:36
			EPO; JPO;	İ
			DERWENT;	
_	. 2	("6232662").PN.	IBM_TDB	2002/05/22
		(0202002).EN.	USPAT;	2003/05/02
			US-PGPUB;	13:13
			EPO; JPO; DERWENT;	
_	2	("6017818").PN.	IBM_TDB USPAT;	2003/05/02
	_	(3027020) 1211.	US-PGPUB;	15:05
				15:05
			EPO; JPO; DERWENT;	
			IBM TDB	
_	10	diffusion near3 barrier near12 (fluorine	USPAT;	2003/05/02
		or F) and interconnect and polymer and	US-PGPUB;	15:16
	1	silicon and (tantalum adj nitride or TaN)	EPO; JPO;	13.10
		and (cobalt or cobalt adj silicide or Co	DERWENT;	
		or CoSi)	IBM TDB	
_	0	diffusion near3 barrier near12 (fluorine	USPAT;	2003/05/02
		or F) and interconnect and polymer adj3	US-PGPUB;	15:18
		(film or layer) and silicon and (tantalum	EPO; JPO;	
		adj nitride or TaN) near12 (cobalt or	DERWENT;	
		cobalt adj silicide or Co or CoSi)	IBM TDB	
-	0	diffusion near3 barrier near12 (fluorine	USPAT;	2003/05/02
		or F) and interconnect and polymer adj3	US-PGPUB;	15:18
		(film or layer) and (si or silicon) and	EPO; JPO;	
		(tantalum adj nitride or TaN) near12	DERWENT;	
		(cobalt or cobalt adj silicide or Co or	IBM_TDB	
		CoSi)	_	
_	116	titanium adj alloy near8 silicide	USPAT;	2003/05/03
			US-PGPUB;	11:26
			EPO; JPO;	
			DERWENT;	
	4-	Additional control of the control of	IBM_TDB	
_	17	titanium adj alloy near1 silicide	USPAT;	2003/05/03
			US-PGPUB;	11:26
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	36	titanium adj alloy near2 silicide	USPAT;	2003/05/03
			US-PGPUB;	12:03
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	